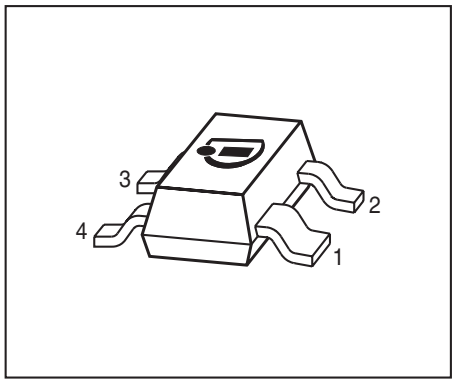
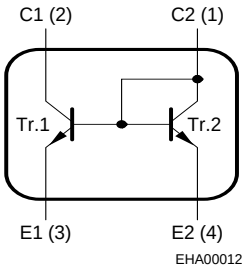
NPN Silicon Double Transistor

- To be used as a current mirror
- Good thermal coupling and V_{BE} matching
- High current gain
- Low collector-emitter saturation voltage
- Pb-free (RoHS compliant) package [1)]
- Qualified according AEC Q101





Type	Marking	Pin Configuration				Package
BCV61	1Js	1 = C2	2 = C1	3 = E1	4 = E2	SOT143
BCV61B	1Ks	1 = C2	2 = C1	3 = E1	4 = E2	SOT143
BCV61C	1Ls	1 = C2	2 = C1	3 = E1	4 = E2	SOT143

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage (transistor T1)	V_{CEO}	30	V
Collector-base voltage (open emitter) (transistor T1)	V_{CBO}	30	
Emitter-base voltage	V_{EBS}	6	
DC collector current	I_C	100	mA
Peak collector current	I_{CM}	200	
Base peak current (transistor T1)	I_{BM}	200	
Total power dissipation, T_S = 99 °C	P_{tot}	300	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

[1]Pb-containing package may be available upon special request

Thermal Resistance

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Junction - soldering point[1]	R_{thJS}		≤170		K/W

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics of T1					
Collector-emitter breakdown voltage I_C = 10 mA, I_B = 0	$V_{(BR)CEO}$	30	-	-	V
Collector-base breakdown voltage I_C = 10 µA, I_E = 0	$V_{(BR)CBO}$	30	-	-	
Emitter-base breakdown voltage I_E = 10 µA, I_C = 0	$V_{(BR)EBO}$	6	-	-	
Collector cutoff current V_{CB} = 30 V, I_E = 0	I_{CBO}	-	-	15	nA
Collector cutoff current V_{CB} = 30 V, I_E = 0 , T_A = 150 °C	I_{CBO}	-	-	5	µA
DC current gain[2] I_C = 0.1 mA, V_{CE} = 5 V	h_{FE}	100	-	-	-
DC current gain[2] I_C = 2 mA, V_{CE} = 5 V BCV61A BCV61B BCV61C	h_{FE}	 110 200 420	 180 290 520	 220 450 800	
Collector-emitter saturation voltage[2] I_C = 10 mA, I_B = 0.5 mA I_C = 100 mA, I_B = 5 mA	V_{CEsat}	 - -	 90 200	 250 600	mV
Base-emitter saturation voltage[2] I_C = 10 mA, I_B = 0.5 mA I_C = 100 mA, I_B = 5 mA	V_{BEsat}	 - -	 700 900	 - -	
Base-emitter voltage[2] I_C = 2 mA, V_{CE} = 5 V I_C = 10 mA, V_{CE} = 5 V	$V_{BE(ON)}$	 580 -	 660 -	 700 770	

[1]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

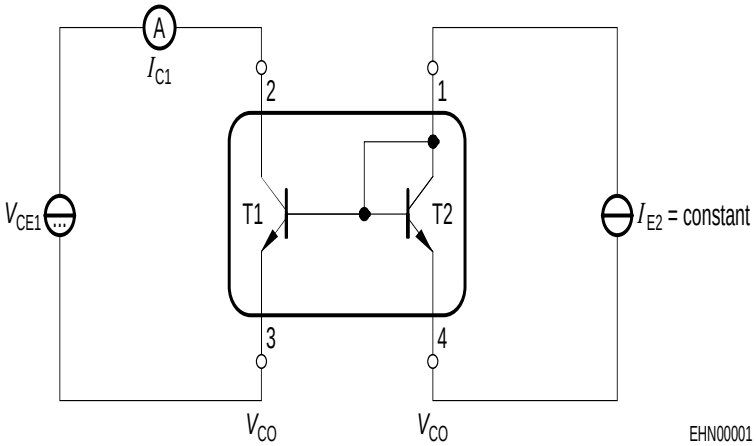
[2]Puls test: $t \leq 300$ µs, D = 2%

Electrical Characteristics at T_A = 25°C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Base-emitter forward voltage	V_{BES}				V
I_E = 10 µA		0.4	-	-	
I_E = 250 mA		-	-	1.8	
Matching of transistor T1 and transistor T2	I_{C1} / I_{C2}				-
at I_{E2} = 0.5mA and V_{CE1} = 5V		-	-	-	
T_A = 25 °C		0.7	-	1.3	
T_A = 150 °C		0.7	-	1.3	
Thermal coupling of transistor T1 and transistor T2 [1] T1: V_{CE} = 5V Maximum current of thermal stability of I_{C1}	I_{E2}	-	5	-	mA
AC characteristics for transistor T1					
Transition frequency	f_T	-	250	-	MHz
I_C = 10 mA, V_{CE} = 5 V, f = 100 MHz					
Collector-base capacitance	C_{cb}	-	0.95	-	pF
V_{CB} = 10 V, f = 1 MHz					
Emitter-base capacitance	C_{eb}	-	9	-	
V_{EB} = 0.5 V, f = 1 MHz					
Noise figure	F	-	2	-	dB
I_C = 200 µA, V_{CE} = 5 V, R_S = 2 kΩ, f = 1 kHz, Δ f = 200 Hz					
Short-circuit input impedance	h_{11e}	-	4.5	-	kΩ
I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz					
Open-circuit reverse voltage transf.ratio	h_{12e}	-	2	-	10^{-4}
I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz					
Short-circuit forward current transf.ratio	h_{21e}	100	-	900	-
I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz					
Open-circuit output admittance	h_{22e}	-	30	-	µS
I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz					

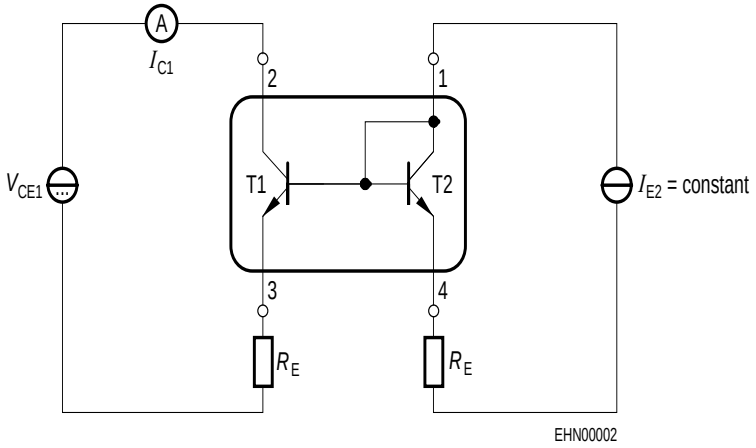
1) Witout emitter resistor. Device mounted on alumina 15mm x 16.5mm x 0.7mm

Test circuit for current matching



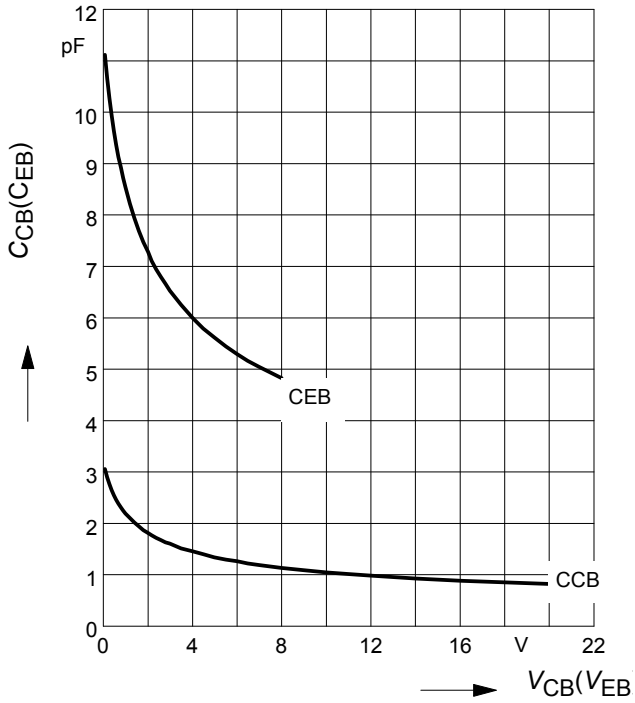
Note: Voltage drop at contacts: V_{CO} < 2/3 V_T = 16mV

Characteristic for determination of V_{CE1} at specified R_E range with I_{E2} as parameter under condition of I_{C1}/I_{E2} = 1.3

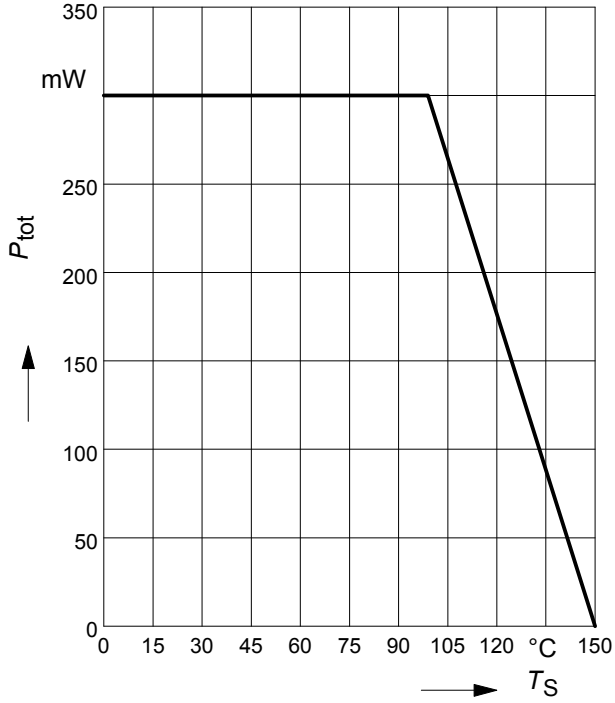


Note: BCV61 with emitter resistors

Collector-base capacitance $C_{cb} = f(V_{CB})$
Emitter-base capacitance $C_{eb} = f(V_{EB})$

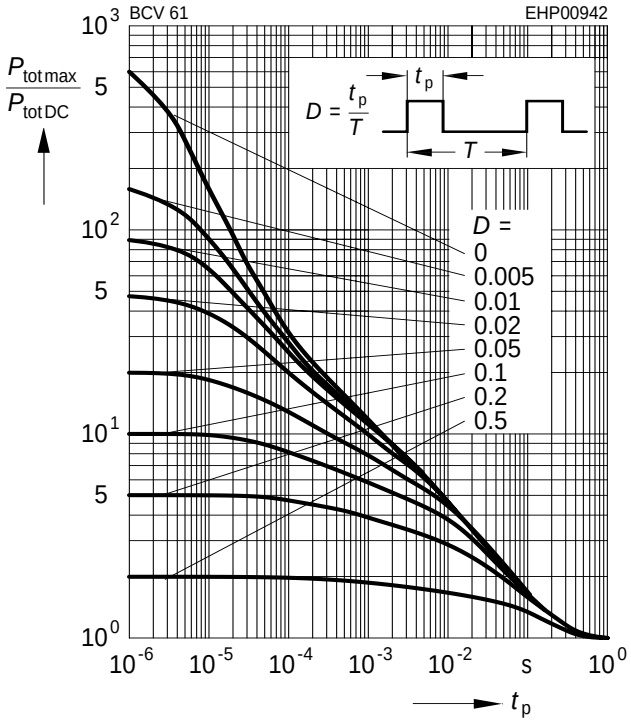


Total power dissipation $P_{tot} = f(T_S)$

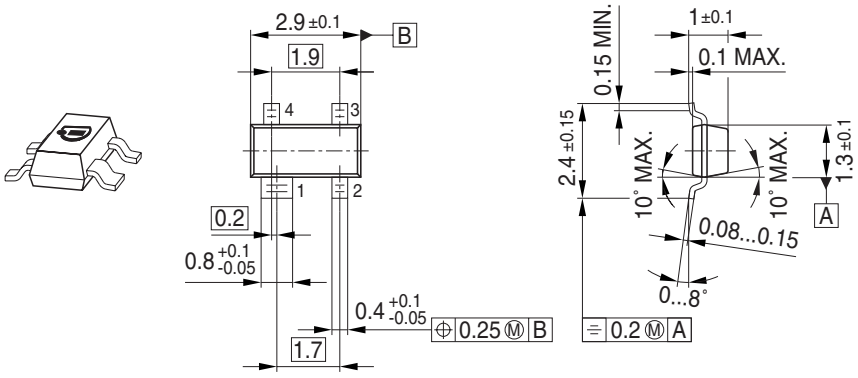


Permissible pulse load

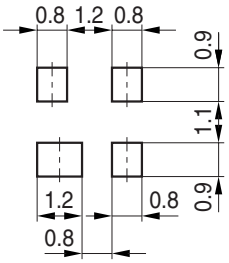
$P_{totmax} / P_{totDC} = f(t_p)$



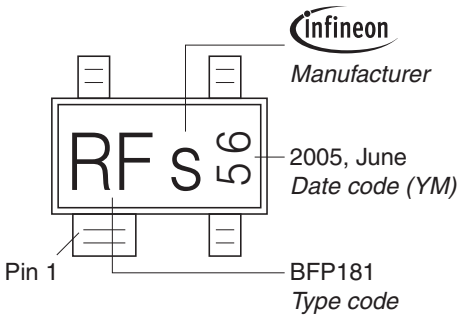
Package Outline



Foot Print

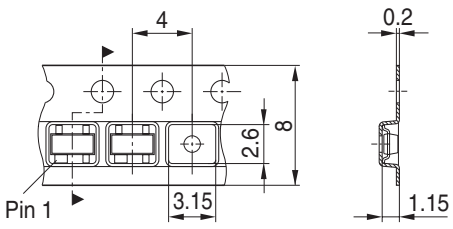


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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